

DRA9A43T

Silicon PNP epitaxial planar type

For digital circuits

Complementary to DRC9A43T

DRA5A43T in SSMini3 type package

■ Features

- High forward current transfer ratio h_{FE} with excellent linearity
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

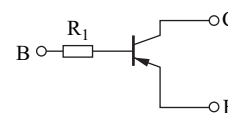
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-50	V
Collector-emitter voltage (Base open)	V_{CEO}	-50	V
Collector current	I_C	-80	mA
Total power dissipation	P_T	125	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Package

- Code
SSMini3-F3-B
- Pin Name
1: Base
2: Emitter
3: Collector

■ Marking Symbol: GF

■ Internal Connection

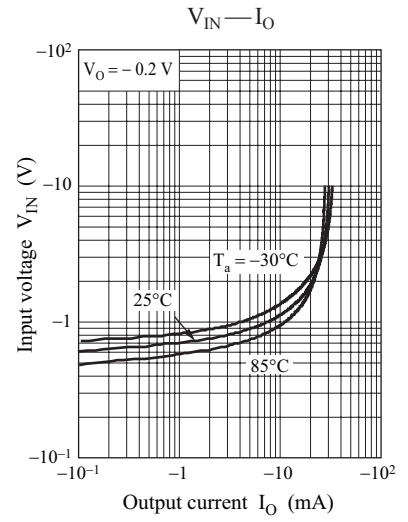
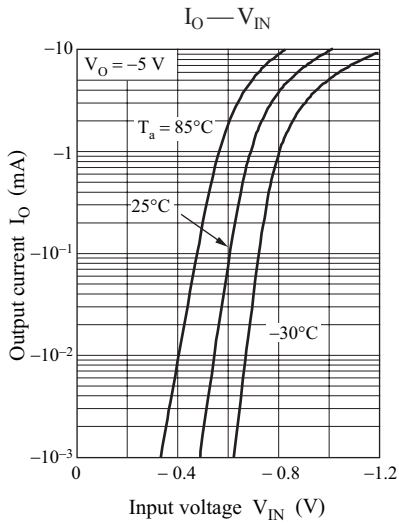
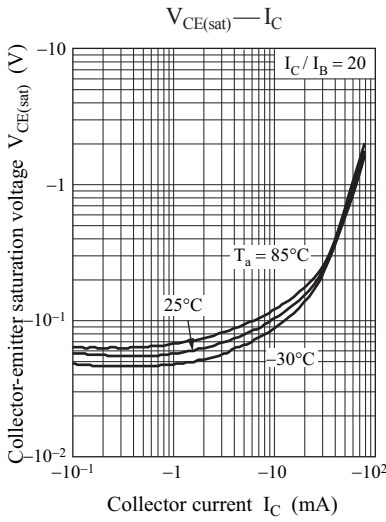
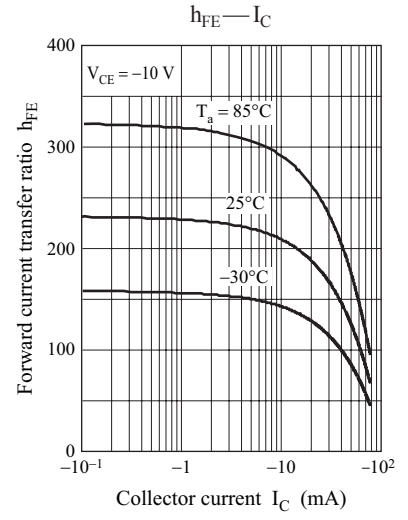
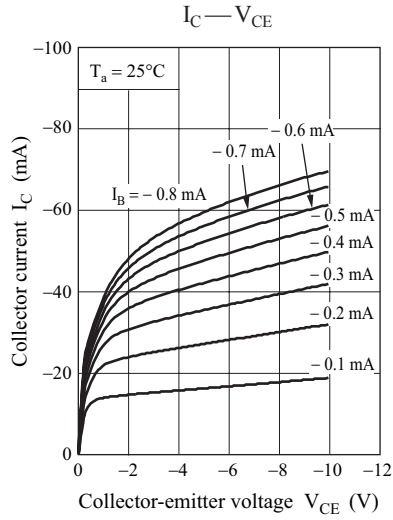
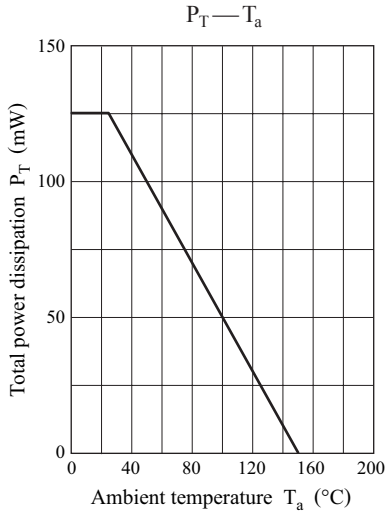


Resistance value	R_1	4.7	k Ω
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■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

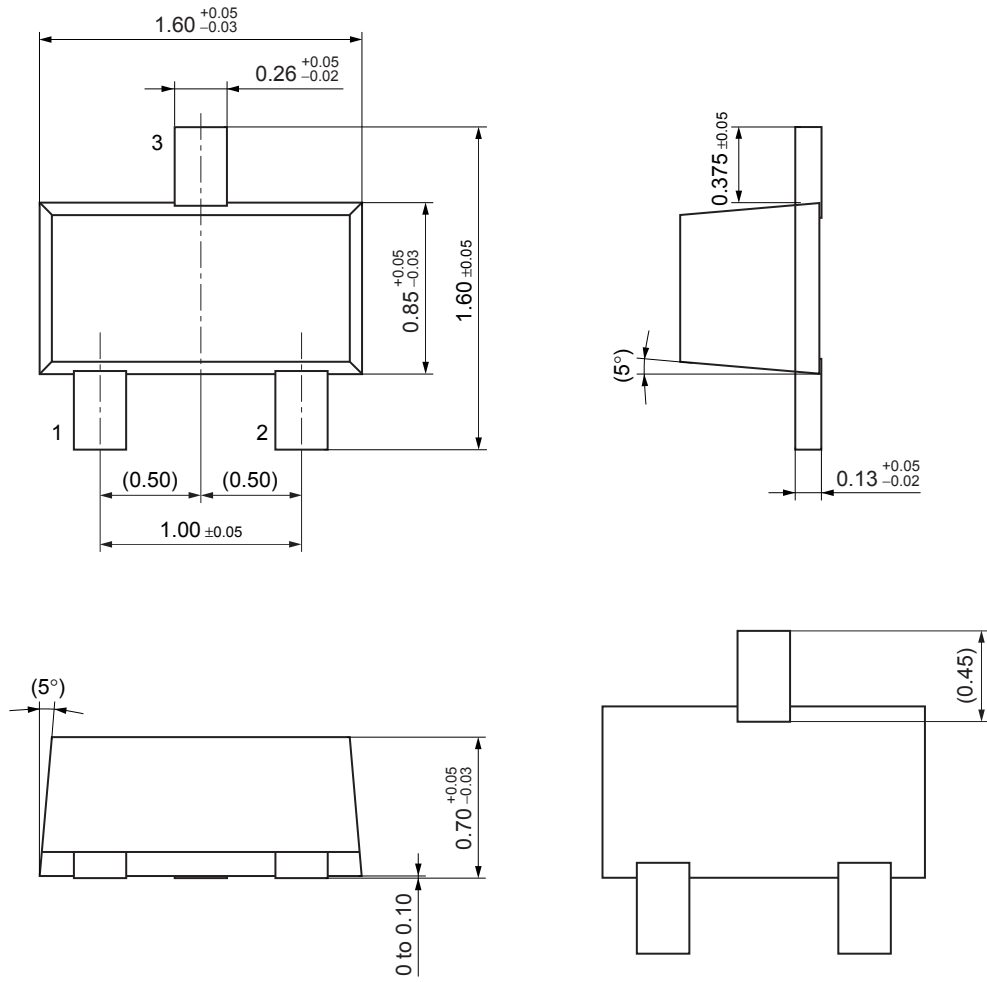
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -2 \text{mA}, I_B = 0$	-50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -50 \text{V}, I_E = 0$			-0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -50 \text{V}, I_B = 0$			-0.5	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -6 \text{V}, I_C = 0$			-0.01	mA
Forward current transfer ratio	h_{FE}	$V_{CE} = -10 \text{V}, I_C = -5 \text{mA}$	160		460	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$			-0.25	V
Input voltage (ON)	$V_{I(on)}$	$V_{CE} = -0.2 \text{V}, I_C = -5 \text{mA}$	-1.0			V
Input voltage (OFF)	$V_{I(off)}$	$V_{CE} = -5 \text{V}, I_C = -100 \mu\text{A}$			-0.4	V
Input resistance	R_1		-30%	4.7	+30%	k Ω

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



SSMini3-F3-B

Unit: mm



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